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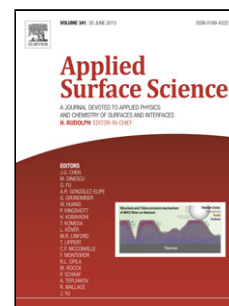
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H₂-Ar dilution for improved c-Si quantum dots in P-doped SiN_x:H thin film matrix

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